

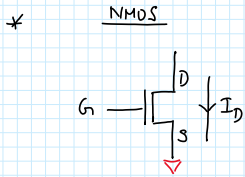
Lecture - 4

* An NMOS device has a threshold voltage $+V_{TN}$ and V_{GS} must be $> V_T$ to turn ON the MOS.

$\therefore V_{GS}$ must be +ve & Hence "Source terminal" of NMOS is always tied to the lowest potential (i.e. GND/ V_{SS} in this case)

* A PMOS device has a threshold Voltage $-V_{TP}$ and $V_{GS} < -V_{TP}$ to turn ON the MOS.

$\therefore V_{GS}$ must be -ve. However, there are only $+V_{DD}$ & V_{SS} available on chip (No negative voltage). \therefore To counter this we tie the "Source terminal" of PMOS is always tied to the highest potential (i.e. V_{DD} in this case) to ensure V_{GS} is negative (i.e. $V_G - V_{DD}$)



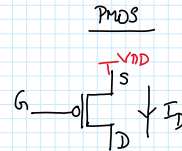
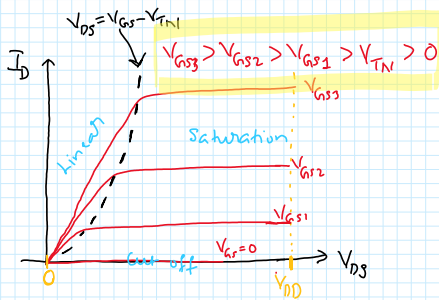
Threshold Voltage: V_{TN}

MOS OFF: $V_{GS} < V_{TN}$

MOS ON: $V_{GS} > V_{TN}$

(i) $V_{DS} < V_{GS} - V_{TN}$: linear

(ii) $V_{DS} \geq V_{GS} - V_{TN}$: Saturation



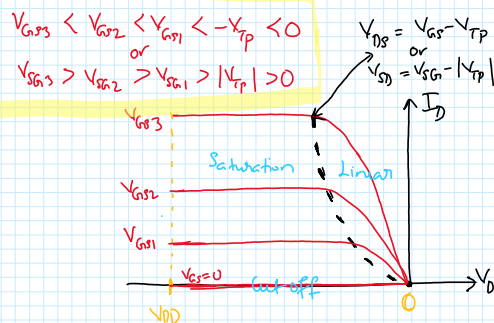
Threshold Voltage: $-V_{TP}$

MOS OFF: $V_{GS} > -V_{TP}$ or $V_{SG} < |V_{TP}|$

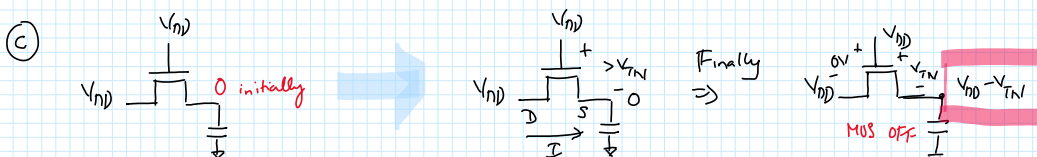
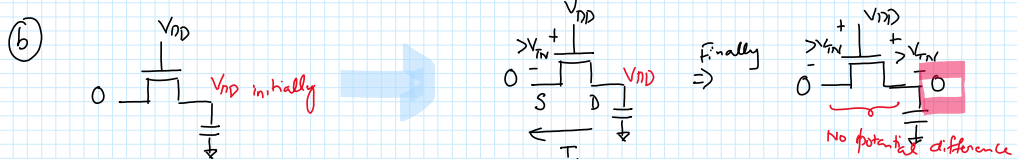
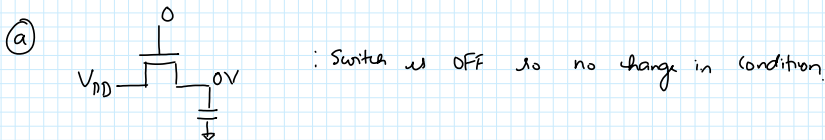
MOS ON: $V_{GS} < -V_{TP}$ or $V_{SG} > |V_{TP}|$

(i) $V_{SD} < V_{SG} - |V_{TP}|$: linear

(ii) $V_{SD} \geq V_{SG} - |V_{TP}|$: Saturation

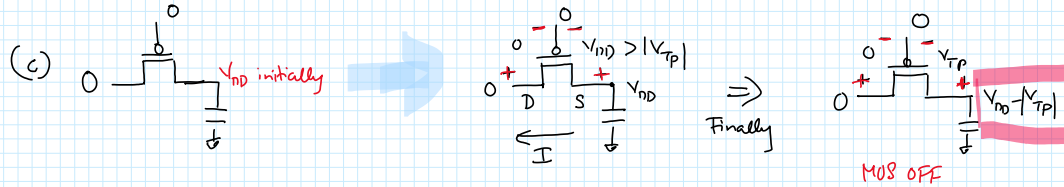
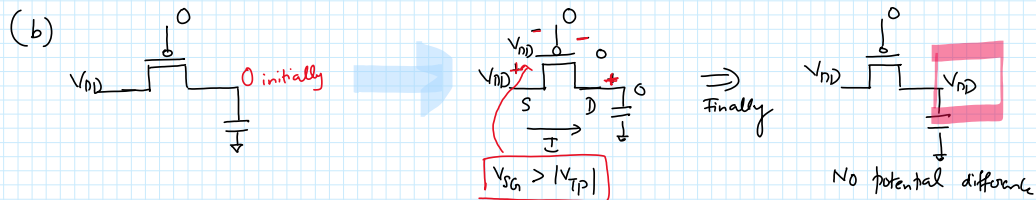
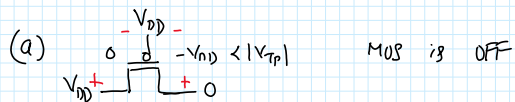


* Consider the cases for NMOS below



For NMOS, $V_o = \min(V_{TN}, V_{DD} - V_{TN})$

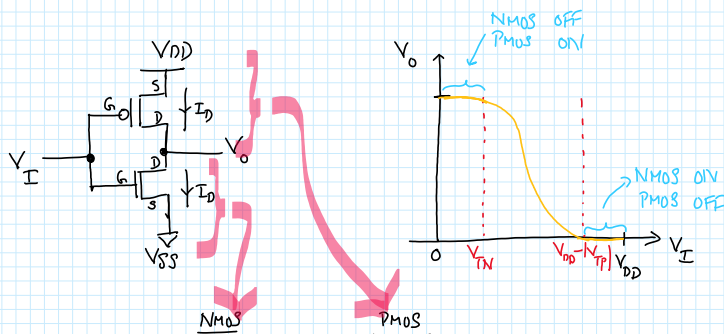
* Consider the cases for PMOS below



* Observations:

- NMOS passes strong logic-0 & weak logic-1 (i.e. o/p is not V_{DD})
- PMOS passes strong logic-1 & weak logic-0 (i.e. o/p is not 0)

* To get a strong logic-0 & logic-1, we can use a combination of NMOS & PMOS



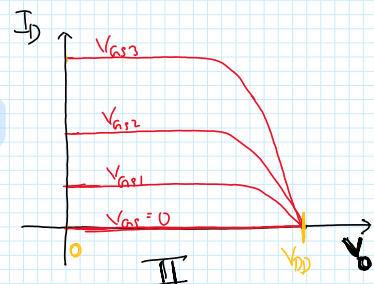
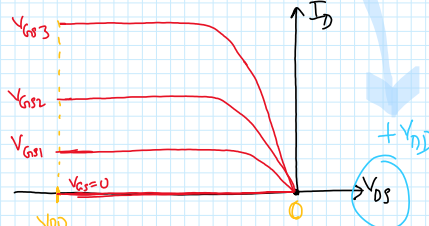
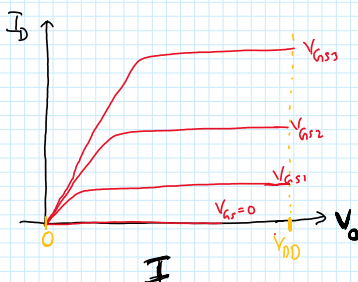
$$V_{DS, NMOS} = V_O$$

$$V_{DS, PMOS} = V_O - V_{DD}$$

* To bring both V_{DS} to same co-ordinate system (w.r.t V_O):

(I) $V_{DS, NMOS} = V_O$

(II) $V_O = V_{DD} + V_{DS, PMOS}$



* To get the operating point (load line) of the inverter, we overlap plot I (for NMOS) & plot II (for PMOS)

